

Vishay Siliconix

N-Channel 40 V (D-S) MOSFET

DESCRIPTION

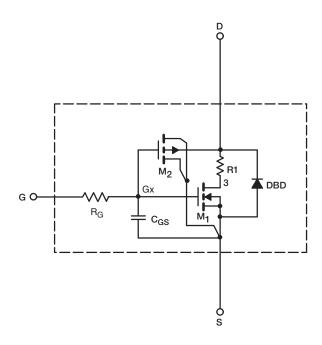
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - $55\,^{\circ}$ C to 125 $^{\circ}$ C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched $C_{\rm gd}$ model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

SUBCIRCUIT MODEL SCHEMATIC



Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



SPICE Device Model Si4122DY

Vishay Siliconix

| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | |
|------------------------------------------------------------------------|---------------------|------------------------------------------------------------------------|----------------|------------------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS | SIMULATED DATA | MEASURED DATA | UNIT |
| Static | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 1.8 | | V |
| Drain-Source On-State Resistance ^a | В | $V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$ | 0.0037 | 0.0036 | Ω |
| | R _{DS(on)} | $V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$ | 0.0049 | 0.0048 | |
| Forward Transconductancea | 9fs | $V_{DS} = 15 \text{ V}, I_D = 15 \text{ A}$ | 59 | 65 | S |
| Diode Forward Voltage ^a | V _{SD} | I _S = 3 A | 0.75 | 0.72 | V |
| Dynamic ^b | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz | 4157 | 4200 | pF |
| Output Capacitance | C _{oss} | | 520 | 475 | |
| Reverse Transfer Capacitance | C _{rss} | | 175 | 225 | |
| Total Gate Charge | | V _{DS} = 20 V, V _{GS} = 10 V, I _D = 10 A | 59 | 62 | nC |
| | Q_g | V _{DS} = 20 V, V _{GS} = 4.5 V, I _D = 10 A | 30 | 29 | |
| Gate-Source Charge | Q _{gs} | | 12 | 12 | |
| Gate-Drain Charge | Q _{gd} | | 9 | 9 | |

Notes

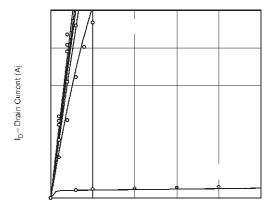
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

R_{US(cn)} – On-Resistance (Ω)

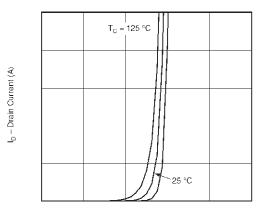
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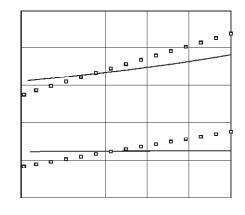
COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25$ °C, unless otherwise noted)



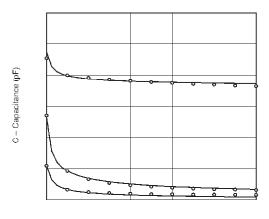
V_{DS} - Drain-to-Source Voltage (V)



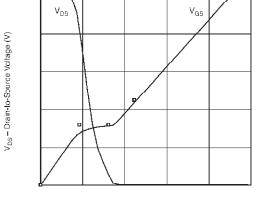
V_{GS} - Gate-to-Source Voltage (V)



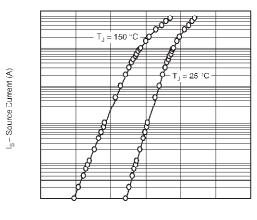
I_D- Drain Current (A)



V_{DS} – Drain-to-Source Voltage (V)







V.... = Source-to-Drain Voltage (V)

Note

• Dots and squares represent measured data.

V_{GS} - Gate-to-Source Vo tage (V)



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